# P-Channel 100-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

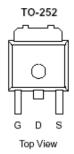
### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-100	205 @ V <sub>GS</sub> = 10V	-13		
-100	250 @ V <sub>GS</sub> = 4.5V	-12		

in





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V <sub>DS</sub>	-100	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	-13	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-50	~		
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>s</sub>	-13	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	50	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ extsf{ heta}JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/ VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

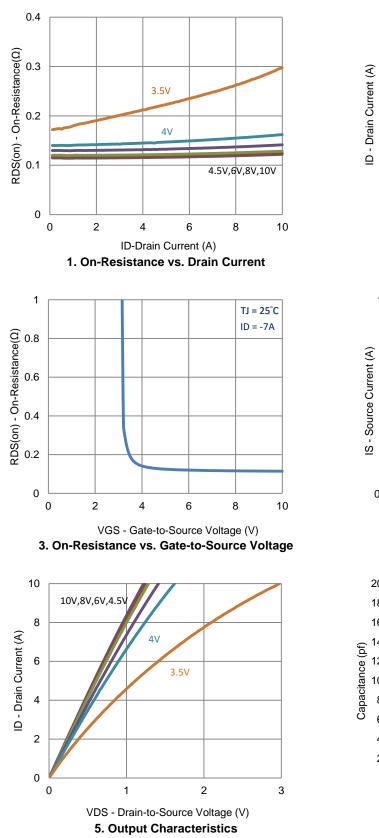
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA	
Zara Cata Valtaga Drain Current		$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$	-		-1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			-10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	-20			Α	
Drain Course On Desistence a	r	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -7 \text{ A}$			205	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -6 \text{ A}$			250		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -7 \text{ A}$		19		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.86		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = -4.5 V,		25		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -50 V$ , $V_{GS} = -4.5 V$ , $I_{D} = -7 A$		6.9			
Gate-Drain Charge	$Q_{gd}$			12		1	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = -50 V, R <sub>1</sub> = 25 Ω,		8			
Rise Time	t <sub>r</sub>	$V_{DS} = -50 V, R_L - 25 \Omega,$ $I_D = -7 A.$		8		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		63		ns	
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = -10$ v, $r_{\text{GEN}} = -0.02$		26			
Input Capacitance	C <sub>iss</sub>			1486			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = -15 V, $V_{GS}$ = 0 V, f = 1 Mhz		127		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	]		104			

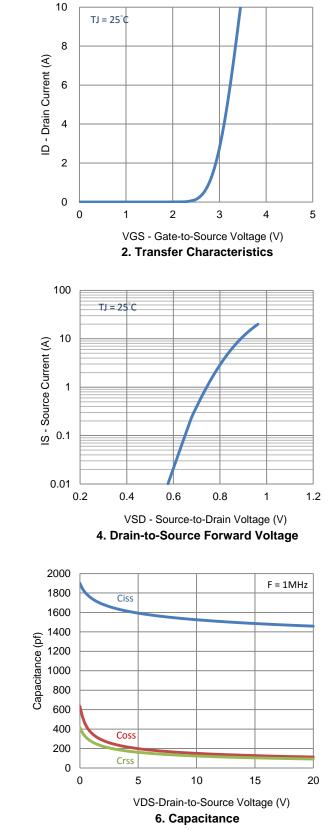
#### Notes

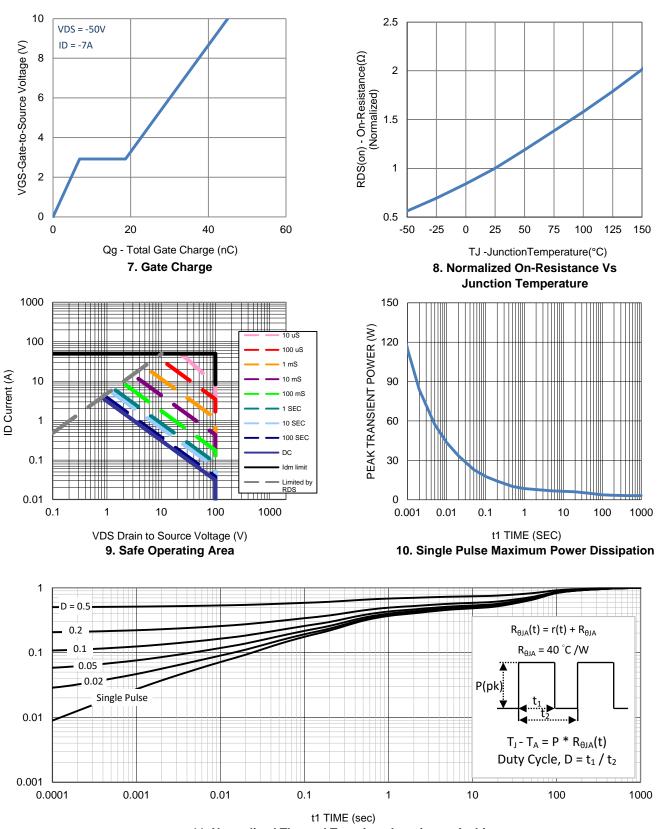
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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## **Typical Electrical Characteristics**



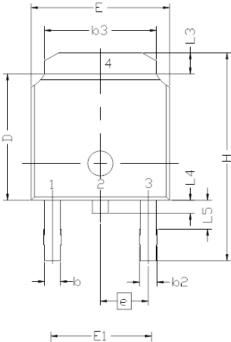


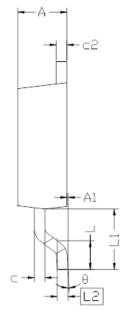
**Typical Electrical Characteristics** 

11. Normalized Thermal Transient Junction to Ambient

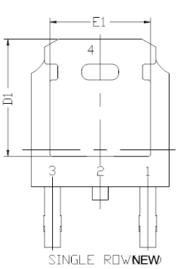
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# **Package Information**





	DIMENIO		DEONTO
SYMBOL	DIMENS: MIN	IUNAL 1 NOM	REQMTS I MAX
F	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2	.743 R	- F
L2	0.	.508 BS	C
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6.223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e		286 BS	
A	2.20	2.30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5.30		
E1	4.40		
θ	0°		10°



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.